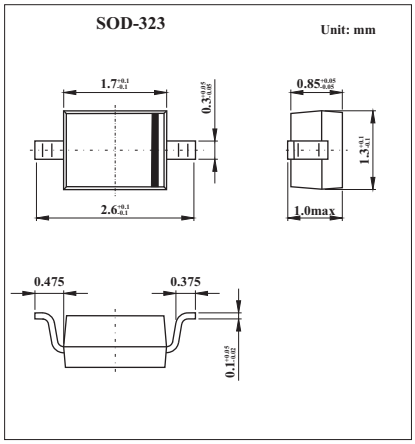
Surface Mount Schottky Barrier Diode

KB160M-20



■ Features

- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Peak repetitive Peak reverse voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	V
RMS Reverse Voltage	$V_{R(RMS)}$	14	V
Average Rectified Output Current (Note 1) @T_L = 90℃	I_O	1	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	25	A
Forward Voltage @I_F = 1.0A @I_F = 3.0A	V_F	0.45 0.75	V
Peak Reverse Current @T_A = 25℃	I_R	1	mA
At Rated DC Blocking Voltage @T_A = 100℃		10	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	℃/W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to 150	℃

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

■ Marking

Marking	SJ

KB160M-20

Typical Characteristics

Fig. 1 - Forward Current Derating Curve

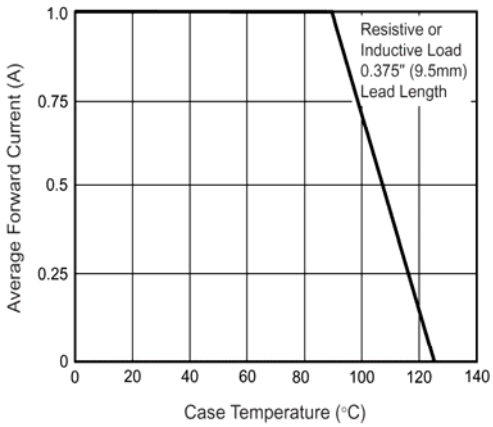


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current

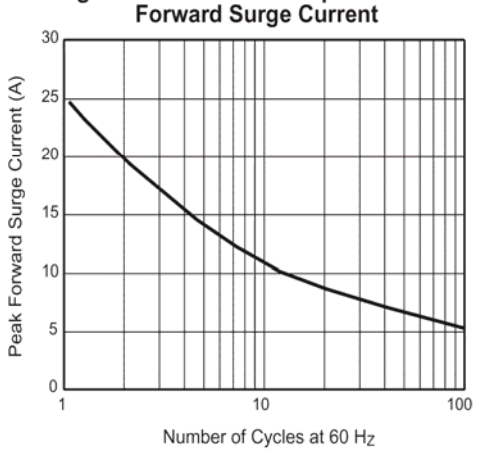


Fig. 3 - Typical Instantaneous Forward Characteristics

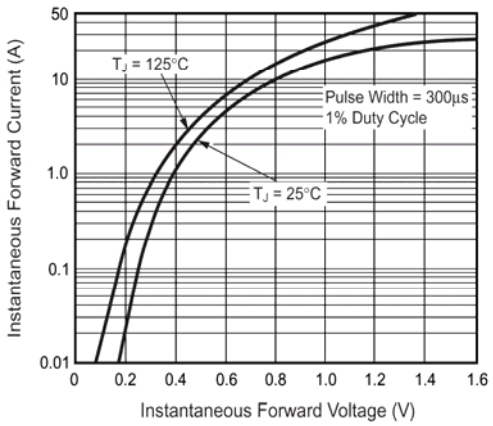


Fig. 4 - Typical Reverse Characteristics

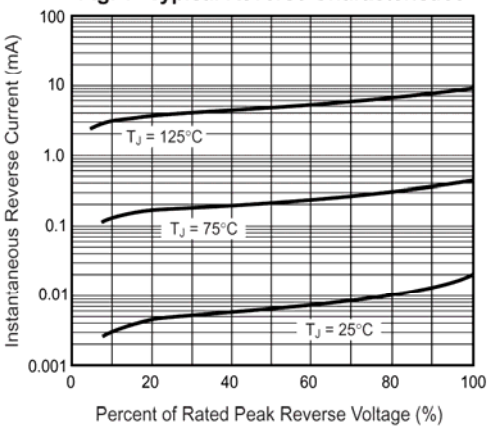


Fig. 5 - Typical Junction Capacitance

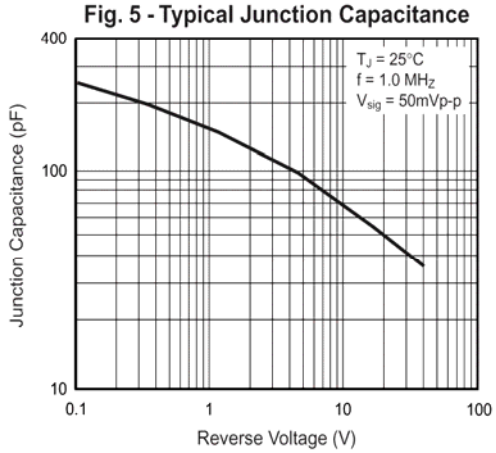


Fig. 6 - Typical Transient Thermal Impedance